CMATVS3V3
CMATVS5V0

SURFACE MOUNT SILICON TRANSIENT VOLTAGE SUPPRESSOR

FEMTOmini™

SOD-923 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMATVS3V3 Series types are Low Leakage, Fast Response TVSs packaged in a space saving SOD-923 surface mount package. These devices are designed to protect sensitive equipment against ESD damage.

MARKING CODES: CMATVS3V3: E
CMATVS5V0: F

APPLICATIONS:

- PDAs
- Memory Card Ports
- Mobile Phones
- Instrumentation

FEATURES:

- Small, **FEMTOmini**™ 1.0 x 0.6 x 0.4mm, SOD-923 Surface Mount Package
- Low Leakage Current
- ESD Protection IEC 61000-4-2: Level 4 (15kV)

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Power Dissipation (8x20μs)	P_{PK}	80	W
ESD Voltage (IEC 61000-4-2)	V_{ESD}	15	kV
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C) V_F=0.9V MAX @ I_F=10mA (for all types)

Type	Maximum Reverse Stand-off Voltage V_{RWM}	Minimum Breakdown Voltage V_{BR} @ I_T	Test Current I_T	Maximum Reverse Leakage Current I_R @ V_{RWM}	Maximum Clamping Voltage V_C @ I_{PP}	Peak Pulse Current I_{PP}	Typical Capacitance @ 0V Bias C
	V	V	mA	μA	V	A	pF
CMATVS3V3	3.3	5.0	1.0	2.5	11	7.0	45
CMATVS5V0	5.0	6.2	1.0	1.0	12.3	7.0	40

R4 (5-January 2012)

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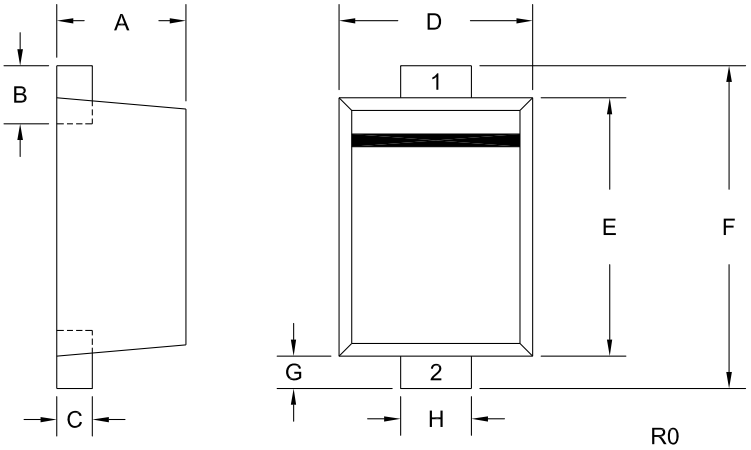
SOD-923 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Cathode
2) Anode

MARKING CODES:
CMATVS3V3: E
CMATVS5V0: F

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.015	0.016	0.39	0.41
B	0.004	0.010	0.10	0.26
C	0.003	0.006	0.08	0.14
D	0.022	0.026	0.55	0.65
E	0.030	0.033	0.75	0.85
F	0.035	0.043	0.90	1.10
G	0.002	0.006	0.05	0.15
H	0.007	0.011	0.17	0.27

SOD-923 (REV: R0)

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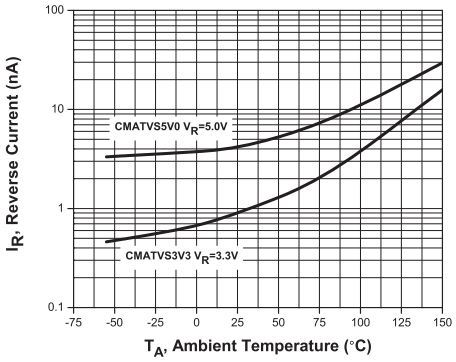
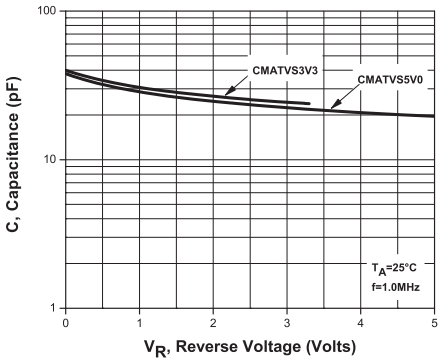
TYPICAL ELECTRICAL CHARACTERISTICS

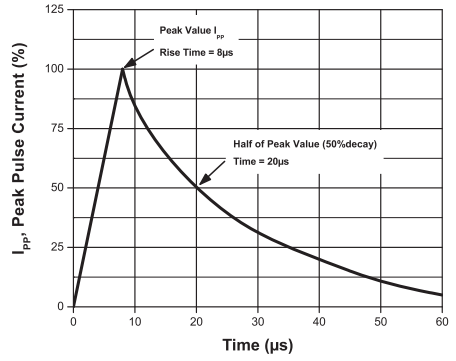
Leakage Current



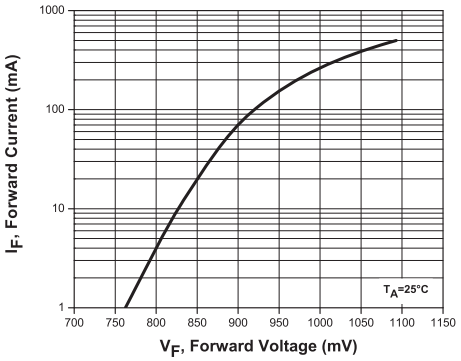
Capacitance



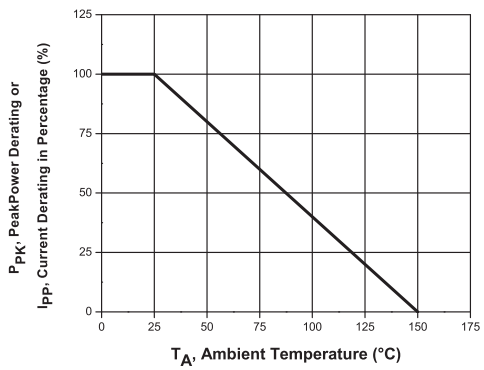
Non-Repetitive Pulse Waveform



Forward Voltage



Normalized Power & Current Derating



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